L Number	Hits	Search Text	DB	Time stamp
1	668	groove) and (thermal adj oxide) and ((silicon or polysilicon or Si) near4 fill\$	USPAT	2003/12/11 13:57
2	224	groove) and (thermal adj oxide) and ((silicon or polysilicon or Si) near4 fill\$	US-PGPUB	2003/12/11 13:57
3	0	and (vapor adj deposition) semiconductor and substrate and (trench or groove) and (thermal adj oxide) and ((silicon or polysilicon or Si) near4 fill\$	EPO )	2003/12/11 13:58
4	0	and (vapor adj deposition)	JPO	2003/12/11 13:58
5	5	and (vapor adj deposition) semiconductor and substrate and (trench or groove) and (thermal adj oxide) and ((silicon or polysilicon or Si) near4 fill\$	DERWENT	2003/12/11 13:58
6	2	and (vapor adj deposition) semiconductor and substrate and (trench or groove) and (thermal adj oxide) and ((silicon or polysilicon or Si) near4 fill\$	IBM_TDB	2003/12/11 13:59
		and (vapor adj deposition)	<u> </u>	

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